Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	667MHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8349zualfb

- Double data rate, DDR1/DDR2 SDRAM memory controller
  — Programmable timing supporting DDR1 and DDR2 SDRAM
  — 32- or 64-bit data interface, up to 400 MHz data rate
  — Up to four physical banks (chip selects), each bank up to 1 Gbyte independently addressable
  — DRAM chip configurations from 64 Mbits to 1 Gbit with ×8/×16 data ports
  — Full error checking and correction (ECC) support
  — Support for up to 16 simultaneous open pages (up to 32 pages for DDR2)
  — Contiguous or discontiguous memory mapping
  — Read-modify-write support
  — Sleep-mode support for SDRAM self refresh
  — Auto refresh
  — On-the-fly power management using CKE
  — Registered DIMM support
  — 2.5-V SSTL2 compatible I/O for DDR1, 1.8-V SSTL2 compatible I/O for DDR2
- Dual three-speed (10/100/1000) Ethernet controllers (TSECs)
  — Dual controllers designed to comply with IEEE 802.3™, 802.3u™, 820.3x™, 802.3z™, 802.3ac™ standards
  — Ethernet physical interfaces:
    – 1000 Mbps IEEE Std. 802.3 GMII/RGMII, IEEE Std. 802.3z TBI/RTBI, full-duplex
    – 10/100 Mbps IEEE Std. 802.3 MII full- and half-duplex
  — Buffer descriptors are backward-compatible with MPC8260 and MPC860T 10/100 programming models
  — 9.6-Kbyte jumbo frame support
  — RMON statistics support
  — Internal 2-Kbyte transmit and 2-Kbyte receive FIFOs per TSEC module
  — MII management interface for control and status
  — Programmable CRC generation and checking
- Dual PCI interfaces
  — Designed to comply with *PCI Specification Revision 2.3*
  — Data bus width options:
    – Dual 32-bit data PCI interfaces operating at up to 66 MHz
    – Single 64-bit data PCI interface operating at up to 66 MHz
  — PCI 3.3-V compatible
  — PCI host bridge capabilities on both interfaces
  — PCI agent mode on PCI1 interface
  — PCI-to-memory and memory-to-PCI streaming
  — Memory prefetching of PCI read accesses and support for delayed read transactions
  — Posting of processor-to-PCI and PCI-to-memory writes

2 Typical power is based on a voltage of V_{DD} = 1.2 V, a junction temperature of T_J = 105°C, and a Dhrystone benchmark application.
3 Thermal solutions may need to design to a value higher than typical power based on the end application, T_A target, and I/O power.
4 Maximum power is based on a voltage of V_{DD} = 1.2 V, worst case process, a junction temperature of T_J = 105°C, and an artificial smoke test.
5 Typical power is based on a voltage of V_{DD} = 1.3 V, a junction temperature of T_J = 105°C, and a Dhrystone benchmark application.
6 Maximum power is based on a voltage of V_{DD} = 1.3 V, worst case process, a junction temperature of T_J = 105°C, and an artificial smoke test.

Table 5 shows the estimated typical I/O power dissipation for MPC8349EA.

Table 5. MPC8349EA Typical I/O Power Dissipation

Interface	Parameter	GV_{DD} (1.8 V)	GV_{DD} (2.5 V)	OV_{DD} (3.3 V)	LV_{DD} (3.3 V)	LV_{DD} (2.5 V)	Unit	Comments
DDR I/O 65% utilization 2.5 V Rs = 20 Ω Rt = 50 Ω 2 pair of clocks	200 MHz, 32 bits	0.31	0.42	—	—	—	W	—
	200 MHz, 64 bits	0.42	0.55	—	—	—	W	—
	266 MHz, 32 bits	0.35	0.5	—	—	—	W	—
	266 MHz, 64 bits	0.47	0.66	—	—	—	W	—
	300 MHz, 32 bits	0.37	0.54	—	—	—	W	—
	300 MHz, 64 bits	0.50	0.7	—	—	—	W	—
	333 MHz, 32 bits	0.39	0.58	—	—	—	W	—
	333 MHz, 64 bits	0.53	0.76	—	—	—	W	—
	400 MHz, 32 bits	0.44	—	—	—	—	—	—
	400 MHz, 64 bits	0.59	—	—	—	—	—	—
PCI I/O load = 30 pF	33 MHz, 64 bits	—	—	0.08	—	—	W	—
	66 MHz, 64 bits	—	—	0.14	—	—	W	—
	33 MHz, 32 bits	—	—	0.04	—	—	W	Multiply by 2 if using 2 ports.
	66 MHz, 32 bits	—	—	0.07	—	—	W	
Local bus I/O load = 25 pF	133 MHz, 32 bits	—	—	0.27	—	—	W	—
	83 MHz, 32 bits	—	—	0.17	—	—	W	—
	66 MHz, 32 bits	—	—	0.14	—	—	W	—
	50 MHz, 32 bits	—	—	0.11	—	—	W	—
TSEC I/O load = 25 pF	MII	—	—	—	0.01	—	W	Multiply by number of interfaces used.
	GMII or TBI	—	—	—	0.06	—	W	
	RGMII or RTBI	—	—	—	—	0.04	W	
USB	12 MHz	—	—	0.01	—	—	W	Multiply by 2 if using 2 ports.
	480 MHz	—	—	0.2	—	—	W	
Other I/O	—	—	—	0.01	—	—	W	—

Table 15 provides the DDR capacitance when GV_{DD}(typ) = 2.5 V.

Table 15. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 16 provides the current draw characteristics for MV_{REF}.

Table 16. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Note
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:

1. The voltage regulator for MV_{REF} must supply up to 500 μA current.

6.2 DDR and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR and DDR2 SDRAM interface.

6.2.1 DDR and DDR2 SDRAM Input AC Timing Specifications

Table 17 provides the input AC timing specifications for the DDR2 SDRAM when GV_{DD}(typ) = 1.8 V.

Table 17. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with GV_{DD} of 1.8 ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V	—

Table 18 provides the input AC timing specifications for the DDR SDRAM when GV_{DD}(typ) = 2.5 V.

Table 18. DDR SDRAM Input AC Timing Specifications for 2.5-V Interface

At recommended operating conditions with GV_{DD} of 2.5 ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.31	—	V	—

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 20 shows the DDR and DDR2 output AC timing specifications.

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) ± 5%.

Parameter	Symbol [1]	Min	Max	Unit	Notes
ADDR/CMD/MODT output setup with respect to MCK	t_{DDKHAS}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		
ADDR/CMD/MODT output hold with respect to MCK	t_{DDKHAX}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		
$\overline{MCS}$(n) output setup with respect to MCK	t_{DDKHCS}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		
$\overline{MCS}$(n) output hold with respect to MCK	t_{DDKHCX}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	—		
MCK to MDQS Skew	t_{DDKHMH}	–0.6	0.6	ns	4
MDQ/MECC/MDM output setup with respect to MDQS	t_{DDKHDS}, t_{DDKLDS}			ps	5
400 MHz		700	—		
333 MHz		775	—		
266 MHz		1100	—		
200 MHz		1200	—		
MDQ/MECC/MDM output hold with respect to MDQS	t_{DDKHDX}, t_{DDKLDX}			ps	5
400 MHz		700	—		
333 MHz		900	—		
266 MHz		1100	—		
200 MHz		1200	—		
MDQS preamble start	t_{DDKHMP}	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	6

Figure 7 shows the DDR SDRAM output timing diagram.

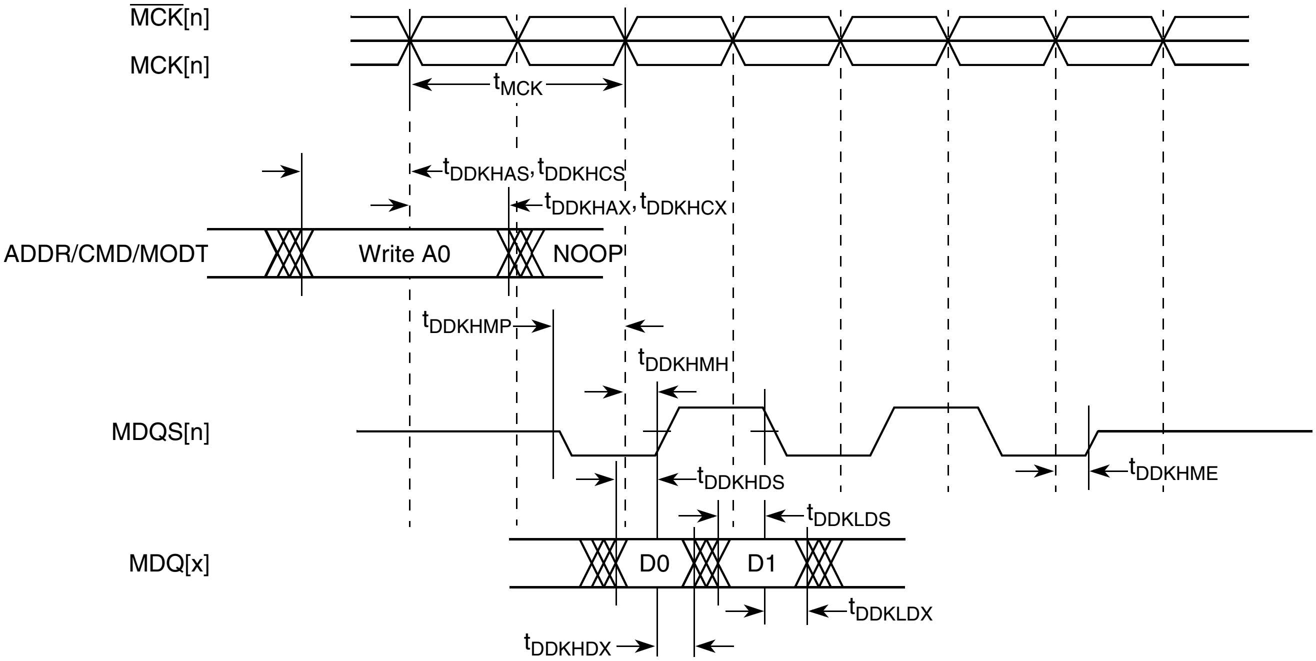


Figure 7. DDR SDRAM Output Timing Diagram

Figure 8 provides the AC test load for the DDR bus.

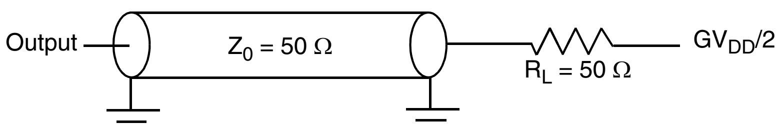


Figure 8. DDR AC Test Load

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8349EA.

7.1 DUART DC Electrical Characteristics

Table 21 provides the DC electrical characteristics for the DUART interface of the MPC8349EA.

Table 21. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (0.8 V ≤ V_{IN} ≤ 2 V)	I_{IN}	—	±5	μA

Table 21. DUART DC Electrical Characteristics (continued)

Parameter	Symbol	Min	Max	Unit
High-level output voltage, $I_{OH} = -100\ \mu A$	V_{OH}	$OV_{DD} - 0.2$	—	V
Low-level output voltage, $I_{OL} = 100\ \mu A$	V_{OL}	—	0.2	V

7.2 DUART AC Electrical Specifications

Table 22 provides the AC timing parameters for the DUART interface of the MPC8349EA.

Table 22. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	256	baud	—
Maximum baud rate	> 1,000,000	baud	1
Oversample rate	16	—	2

Notes:
1. Actual attainable baud rate will be limited by the latency of interrupt processing.
2. The middle of a start bit is detected as the 8^{th} sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16^{th} sample.

8 Ethernet: Three-Speed Ethernet, MII Management

This section provides the AC and DC electrical characteristics for three-speeds (10/100/1000 Mbps) and MII management.

8.1 Three-Speed Ethernet Controller (TSEC)—GMII/MII/TBI/RGMII/RTBI Electrical Characteristics

The electrical characteristics specified here apply to gigabit media independent interface (GMII), the media independent interface (MII), ten-bit interface (TBI), reduced gigabit media independent interface (RGMII), and reduced ten-bit interface (RTBI) signals except management data input/output (MDIO) and management data clock (MDC). The MII, GMII, and TBI interfaces are defined for 3.3 V, and the RGMII and RTBI interfaces are defined for 2.5 V. The RGMII and RTBI interfaces follow the Hewlett-Packard *Reduced Pin-Count Interface for Gigabit Ethernet Physical Layer Device Specification*, Version 1.2a (9/22/2000). The electrical characteristics for MDIO and MDC are specified in Section 8.3, “Ethernet Management Interface Electrical Characteristics.”

8.1.1 TSEC DC Electrical Characteristics

GMII, MII, TBI, RGMII, and RTBI drivers and receivers comply with the DC parametric attributes specified in Table 23 and Table 24. The RGMII and RTBI signals in Table 24 are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 23. GMII/TBI and MII DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage 3.3 V	LV_{DD} [2]	—		2.97	3.63	V
Output high voltage	V_{OH}	I_{OH} = –4.0 mA	LV_{DD} = Min	2.40	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 4.0 mA	LV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—	—	2.0	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	—	–0.3	0.90	V
Input high current	I_{IH}	V_{IN} [1] = LV_{DD}		—	40	μA
Input low current	I_{IL}	V_{IN} [1] = GND		–600	—	μA

Notes:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.
2. GMII/MII pins not needed for RGMII or RTBI operation are powered by the OV_{DD} supply.

Table 24. RGMII/RTBI (When Operating at 2.5 V) DC Electrical Characteristics

Parameters	Symbol	Conditions		Min	Max	Unit
Supply voltage 2.5 V	LV_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.00	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND – 0.3	0.40	V
Input high voltage	V_{IH}	—	LV_{DD} = Min	1.7	LV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	LV_{DD} = Min	–0.3	0.70	V
Input high current	I_{IH}	V_{IN} [1] = LV_{DD}		—	10	μA
Input low current	I_{IL}	V_{IN} [1] = GND		–15	—	μA

Note:
1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.2 GMII, MII, TBI, RGMII, and RTBI AC Timing Specifications

The AC timing specifications for GMII, MII, TBI, RGMII, and RTBI are presented in this section.

8.2.1 GMII Timing Specifications

This section describes the GMII transmit and receive AC timing specifications.

Figure 21 through Figure 26 show the local bus signals.

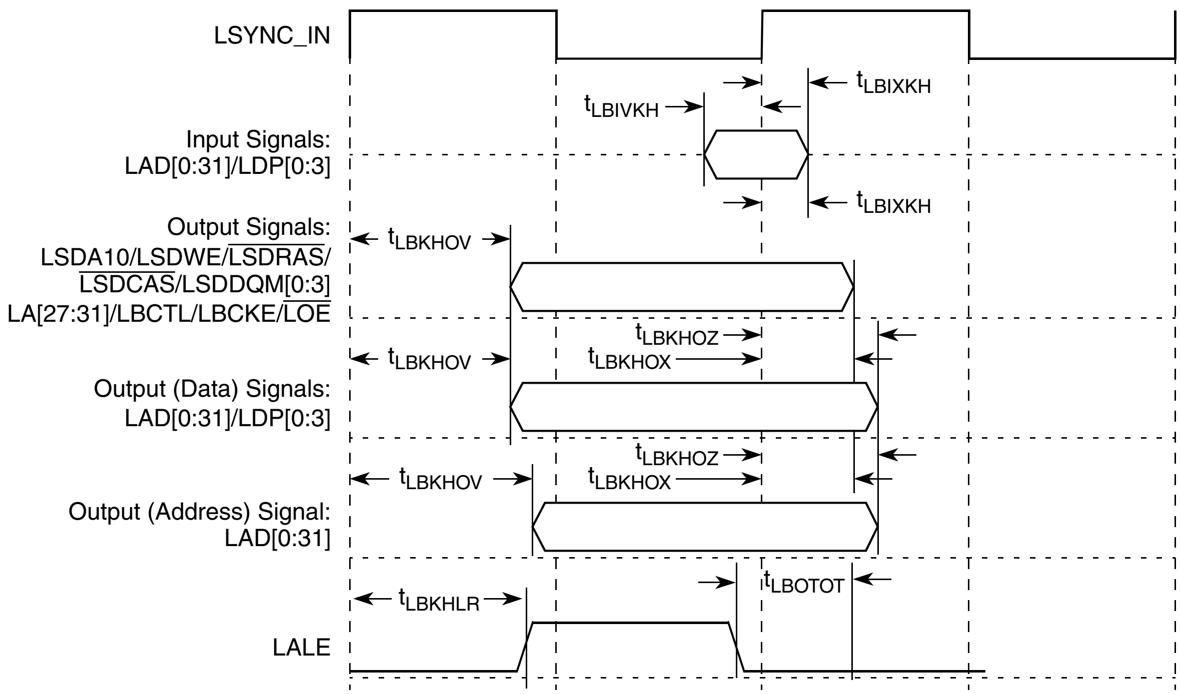


Figure 21. Local Bus Signals, Nonspecial Signals Only (DLL Enabled)

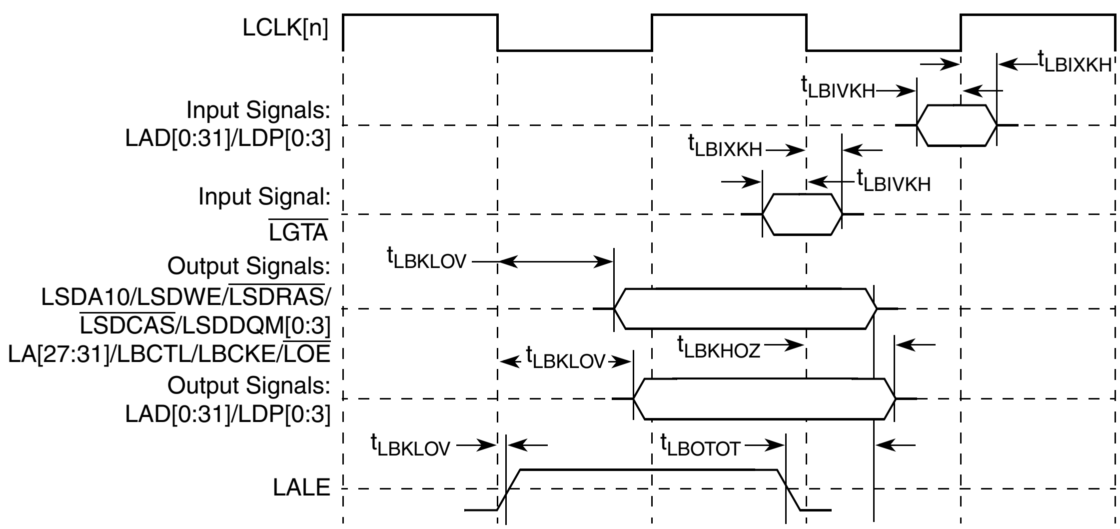


Figure 22. Local Bus Signals, Nonspecial Signals Only (DLL Bypass Mode)

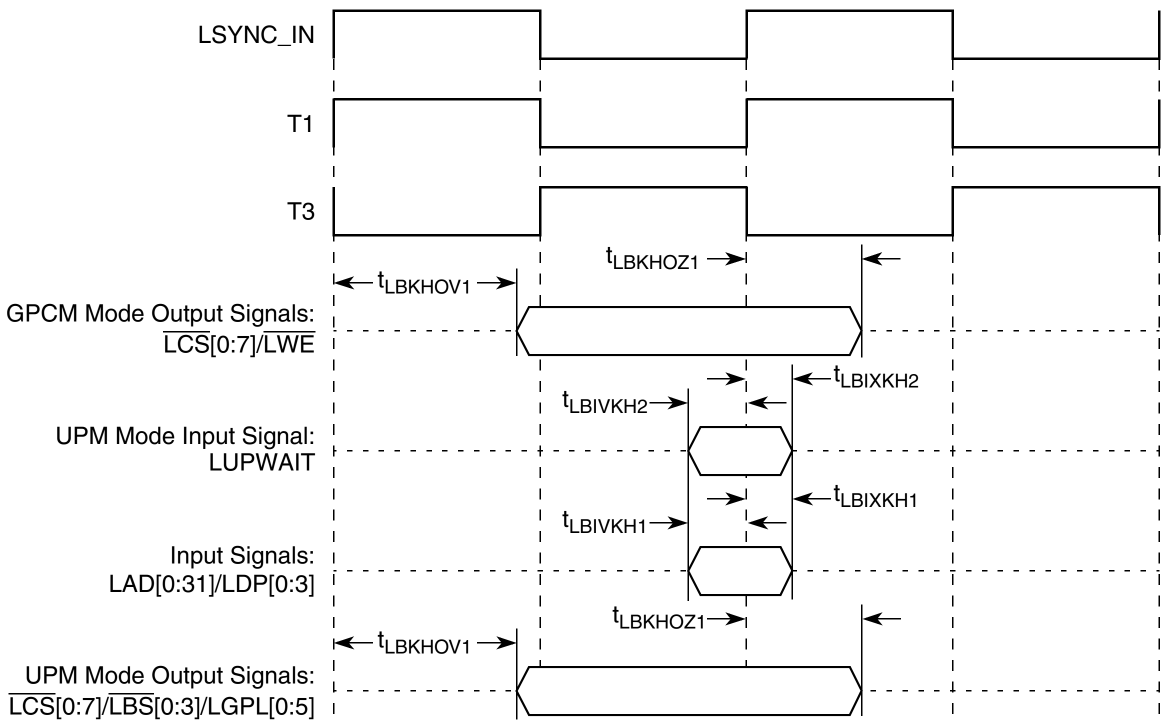


Figure 23. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Enabled)

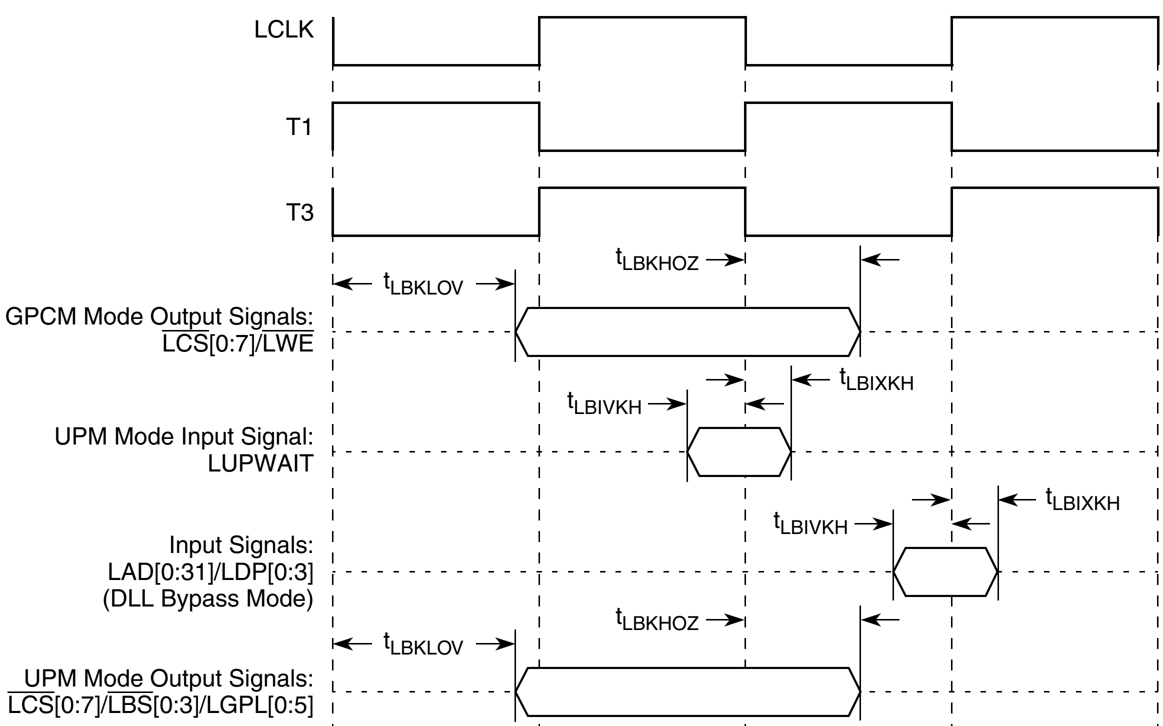


Figure 24. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Bypass Mode)

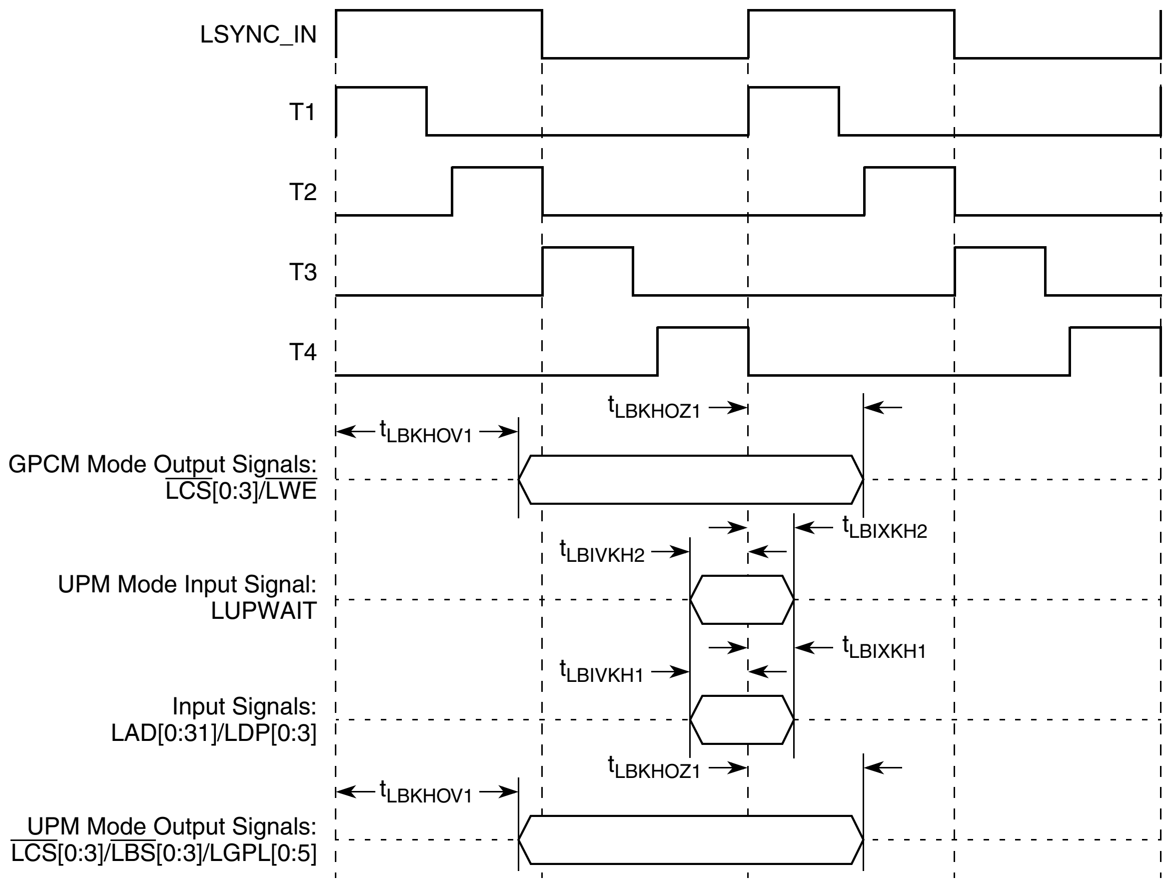


Figure 26. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (DLL Enabled)

11 JTAG

This section describes the DC and AC electrical specifications for the IEEE Std. 1149.1 (JTAG) interface of the MPC8349EA.

11.1 JTAG DC Electrical Characteristics

Table 40 provides the DC electrical characteristics for the IEEE Std. 1149.1 (JTAG) interface of the MPC8349EA.

Table 40. JTAG Interface DC Electrical Characteristics

Parameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	OV_{DD} – 0.3	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V

Figure 30 provides the boundary-scan timing diagram.

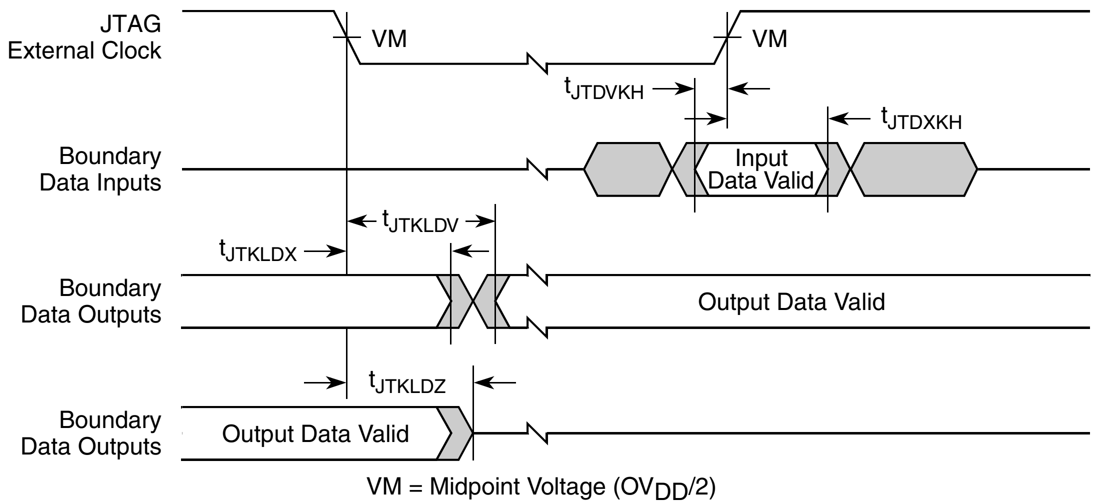


Figure 30. Boundary-Scan Timing Diagram

Figure 31 provides the test access port timing diagram.

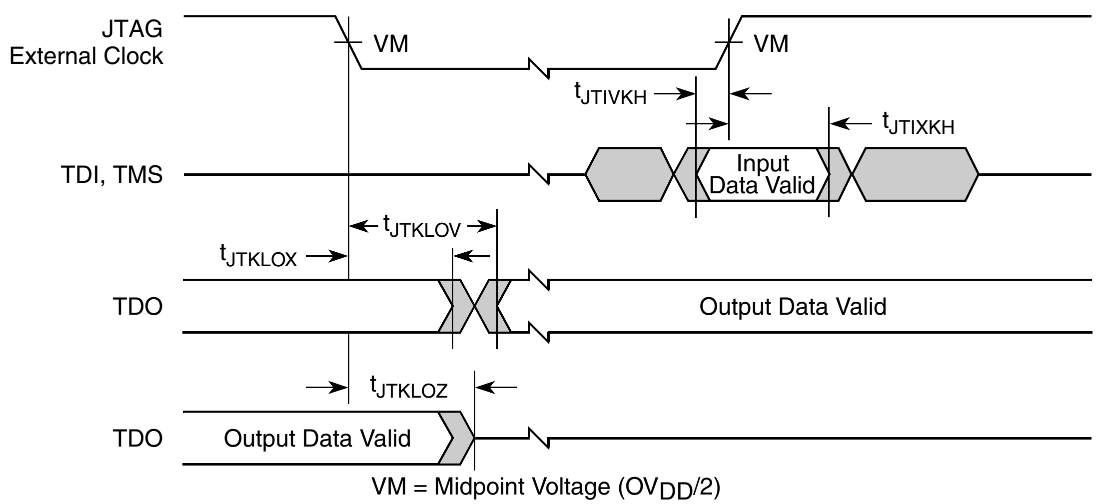


Figure 31. Test Access Port Timing Diagram

Table 47. Timer DC Electrical Characteristics (continued)

Parameter	Symbol	Condition	Min	Max	Unit
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

14.2 Timer AC Timing Specifications

Table 48 provides the timer input and output AC timing specifications.

Table 48. Timers Input AC Timing Specifications[1]

Parameter	Symbol[2]	Min	Unit
Timers inputs—minimum pulse width	t_{TIWID}	20	ns

Notes:

1. Input specifications are measured from the 50 percent level of the signal to the 50 percent level of the rising edge of CLKIN. Timings are measured at the pin.
2. Timer inputs and outputs are asynchronous to any visible clock. Timer outputs should be synchronized before use by external synchronous logic. Timer inputs are required to be valid for at least t_{TIWID} ns to ensure proper operation.

15 GPIO

This section describes the DC and AC electrical specifications for the GPIO.

15.1 GPIO DC Electrical Characteristics

Table 49 provides the DC electrical characteristics for the MPC8349EA GPIO.

Table 49. GPIO DC Electrical Characteristics

PArameter	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Figure 37 provides the AC test load for the SPI.

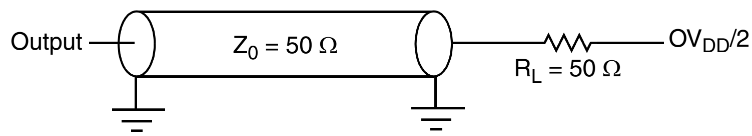
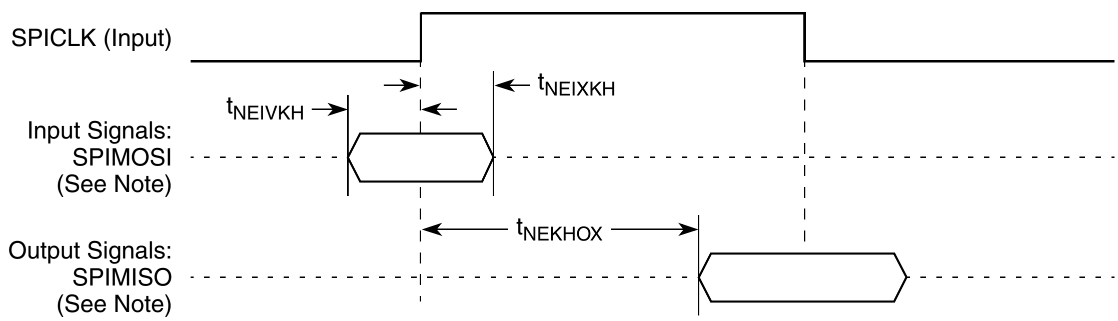


Figure 37. SPI AC Test Load

Figure 38 and Figure 39 represent the AC timings from Table 54. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

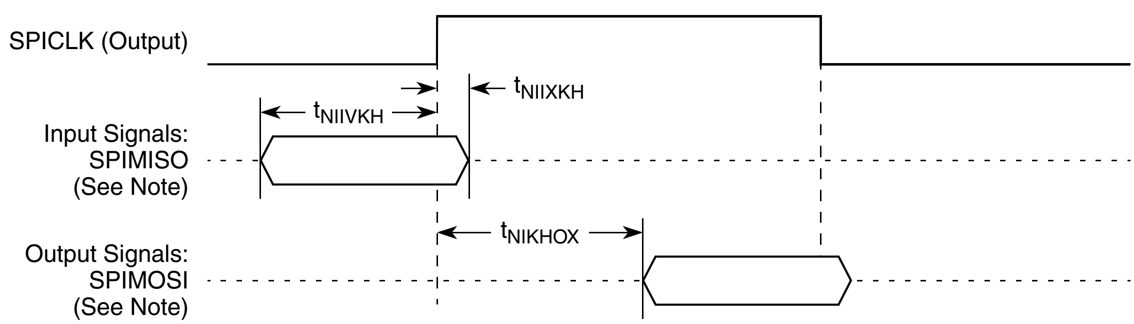
Figure 38 shows the SPI timings in slave mode (external clock).



Note: The clock edge is selectable on SPI.

Figure 38. SPI AC Timing in Slave Mode (External Clock) Diagram

Figure 39 shows the SPI timings in master mode (internal clock).



Note: The clock edge is selectable on SPI.

Figure 39. SPI AC Timing in Master Mode (Internal Clock) Diagram

18 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8349EA is available in a tape ball grid array (TBGA). See Section 18.1, "Package Parameters for the MPC8349EA TBGA" and Section 18.2, "Mechanical Dimensions for the MPC8349EA TBGA.

Table 55. MPC8349EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{PCI2\_FRAME}$/GPIO2[1]	AE33	I/O	OV_{DD}	5
$\overline{PCI2\_TRDY}$/GPIO2[2]	AF32	I/O	OV_{DD}	5
$\overline{PCI2\_IRDY}$/GPIO2[3]	AE34	I/O	OV_{DD}	5
$\overline{PCI2\_STOP}$/GPIO2[4]	AF34	I/O	OV_{DD}	5
$\overline{PCI2\_DEVSEL}$/GPIO2[5]	AF33	I/O	OV_{DD}	5
$\overline{PCI2\_SERR}$/$\overline{PCI1\_ACK64}$	AG33	I/O	OV_{DD}	5
$\overline{PCI2\_PERR}$/$\overline{PCI1\_REQ64}$	AG32	I/O	OV_{DD}	5
$\overline{PCI2\_REQ}$[0:2]/GPIO2[6:8]	Y32, Y34, AA32	I/O	OV_{DD}	—
$\overline{PCI2\_GNT}$[0:2]/GPIO2[9:11]	Y31, Y33, AA31	I/O	OV_{DD}	—
M66EN	A19	I	OV_{DD}	—
DDR SDRAM Memory Interface				
MDQ[0:63]	D5, A3, C3, D3, C4, B3, C2, D4, D2, E5, G2, H6, E4, F3, G4, G3, H1, J2, L6, M6, H2, K6, L2, M4, N2, P4, R2, T4, P6, P3, R1, T2, AB5, AA3, AD6, AE4, AB4, AC2, AD3, AE6, AE3, AG4, AK5, AK4, AE2, AG6, AK3, AK2, AL2, AL1, AM5, AP5, AM2, AN1, AP4, AN5, AJ7, AN7, AM8, AJ9, AP6, AL7, AL9, AN8	I/O	GV_{DD}	—
MECC[0:4]/MSRCID[0:4]	W4, W3, Y3, AA6, T1	I/O	GV_{DD}	—
MECC[5]/MDVAL	U1	I/O	GV_{DD}	—
MECC[6:7]	Y1, Y6	I/O	GV_{DD}	—
MDM[0:8]	B1, F1, K1, R4, AD4, AJ1, AP3, AP7, Y4	O	GV_{DD}	—
MDQS[0:8]	B2, F5, J1, P2, AC1, AJ2, AN4, AL8, W2	I/O	GV_{DD}	—
MBA[0:1]	AD1, AA5	O	GV_{DD}	—
MA[0:14]	W1, U4, T3, R3, P1, M1, N1, L3, L1, K2, Y2, K3, J3, AP2, AN6	O	GV_{DD}	—
$\overline{MWE}$	AF1	O	GV_{DD}	—
$\overline{MRAS}$	AF4	O	GV_{DD}	—
$\overline{MCAS}$	AG3	O	GV_{DD}	—
$\overline{MCS}$[0:3]	AG2, AG1, AK1, AL4	O	GV_{DD}	—
MCKE[0:1]	H3, G1	O	GV_{DD}	3
MCK[0:5]	U2, F4, AM3, V3, F2, AN3	O	GV_{DD}	—
$\overline{MCK}$[0:5]	U3, E3, AN2, V4, E1, AM4	O	GV_{DD}	—
MODT[0:3]	AH3, AJ5, AH1, AJ4	O	GV_{DD}	—

Table 55. MPC8349EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Gigabit Reference Clock				
EC_GTX_CLK125	C8	I	LV_{DD1}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 1)				
TSEC1_COL/GPIO2[20]	A17	I/O	OV_{DD}	—
TSEC1_CRS/GPIO2[21]	F12	I/O	LV_{DD1}	—
TSEC1_GTX_CLK	D10	O	LV_{DD1}	3
TSEC1_RX_CLK	A11	I	LV_{DD1}	—
TSEC1_RX_DV	B11	I	LV_{DD1}	—
TSEC1_RX_ER/GPIO2[26]	B17	I/O	OV_{DD}	—
TSEC1_RXD[7:4]/GPIO2[22:25]	B16, D16, E16, F16	I/O	OV_{DD}	—
TSEC1_RXD[3:0]	E10, A8, F10, B8	I	LV_{DD1}	—
TSEC1_TX_CLK	D17	I	OV_{DD}	—
TSEC1_TXD[7:4]/GPIO2[27:30]	A15, B15, A14, B14	I/O	OV_{DD}	—
TSEC1_TXD[3:0]	A10, E11, B10, A9	O	LV_{DD1}	10
TSEC1_TX_EN	B9	O	LV_{DD1}	—
TSEC1_TX_ER/GPIO2[31]	A16	I/O	OV_{DD}	—
Three-Speed Ethernet Controller (Gigabit Ethernet 2)				
TSEC2_COL/GPIO1[21]	C14	I/O	OV_{DD}	—
TSEC2_CRS/GPIO1[22]	D6	I/O	LV_{DD2}	—
TSEC2_GTX_CLK	A4	O	LV_{DD2}	—
TSEC2_RX_CLK	B4	I	LV_{DD2}	—
TSEC2_RX_DV/GPIO1[23]	E6	I/O	LV_{DD2}	—
TSEC2_RXD[7:4]/GPIO1[26:29]	A13, B13, C13, A12	I/O	OV_{DD}	—
TSEC2_RXD[3:0]/GPIO1[13:16]	D7, A6, E8, B7	I/O	LV_{DD2}	—
TSEC2_RX_ER/GPIO1[25]	D14	I/O	OV_{DD}	—
TSEC2_TXD[7]/GPIO1[31]	B12	I/O	OV_{DD}	—
TSEC2_TXD[6]/ DR_XCVR_TERM_SEL	C12	O	OV_{DD}	—
TSEC2_TXD[5]/ DR_UTMI_OPMODE1	D12	O	OV_{DD}	—
TSEC2_TXD[4]/ DR_UTMI_OPMODE0	E12	O	OV_{DD}	—
TSEC2_TXD[3:0]/GPIO1[17:20]	B5, A5, F8, B6	I/O	LV_{DD2}	—

19 Clocking

Figure 41 shows the internal distribution of the clocks.

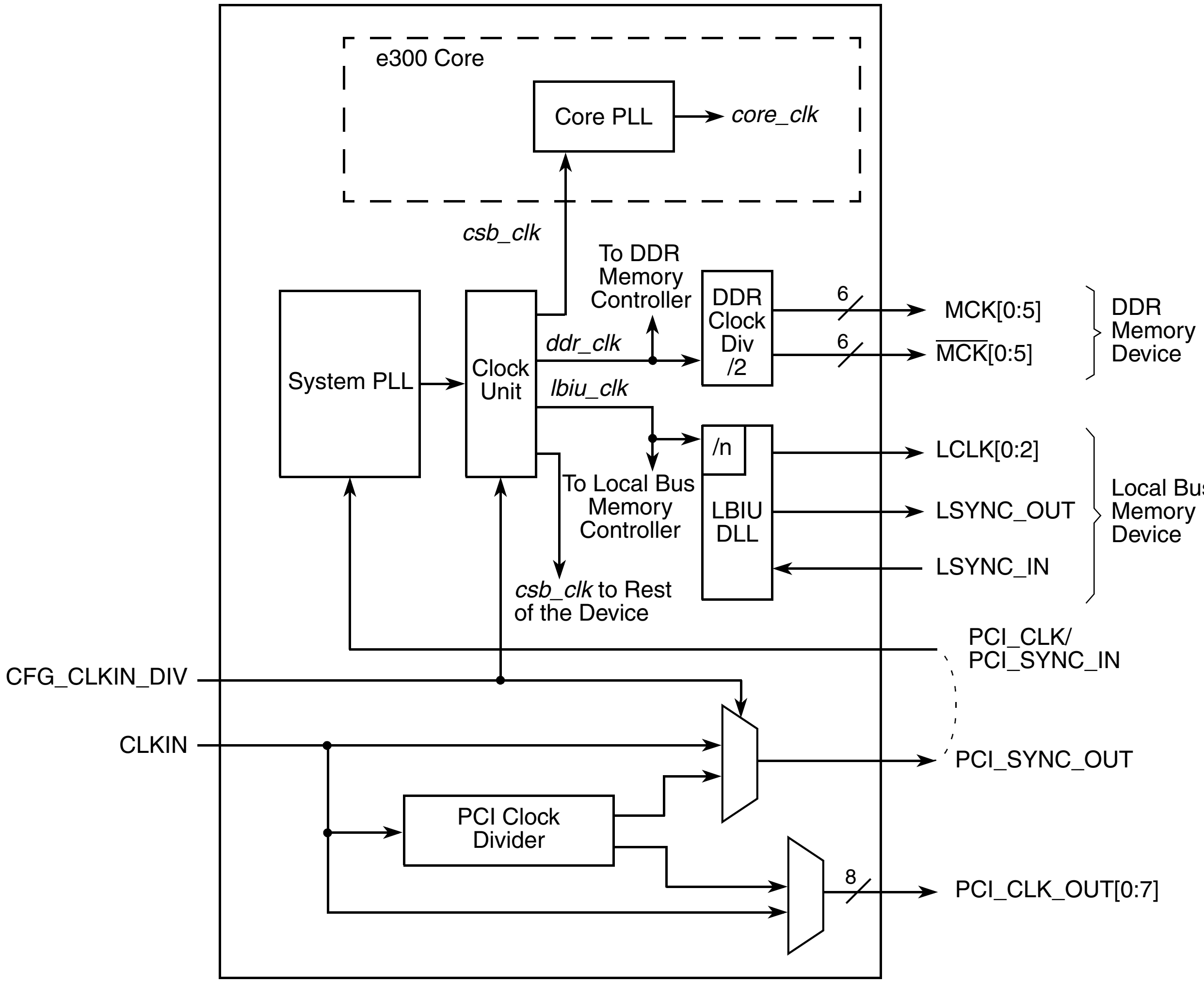


Figure 41. MPC8349EA Clock Subsystem

The primary clock source can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. When the MPC8349EA is configured as a PCI host device, CLKIN is its primary input clock. CLKIN feeds the PCI clock divider (÷2) and the multiplexors for PCI_SYNC_OUT and PCI_CLK_OUT. The CFG_CLKIN_DIV configuration input selects whether CLKIN or CLKIN/2 is driven out on the PCI_SYNC_OUT signal. The OCCR[PCICD*n*] parameters select whether CLKIN or CLKIN/2 is driven out on the PCI_CLK_OUT*n* signals.

PCI_SYNC_OUT is connected externally to PCI_SYNC_IN to allow the internal clock subsystem to synchronize to the system PCI clocks. PCI_SYNC_OUT must be connected properly to PCI_SYNC_IN, with equal delay to all PCI agent devices in the system, to allow the MPC8349EA to function. When the device is configured as a PCI agent device, PCI_CLK is the primary input clock and the CLKIN signal should be tied to GND.

As shown in Figure 41, the primary clock input (frequency) is multiplied up by the system phase-locked loop (PLL) and the clock unit to create the coherent system bus clock (*csb_clk*), the internal clock for the DDR controller (*ddr_clk*), and the internal clock for the local bus interface unit (*lbiu_clk*).

The *csb_clk* frequency is derived from a complex set of factors that can be simplified into the following equation:

csb_clk = {PCI_SYNC_IN × (1 + CFG_CLKIN_DIV)} × SPMF

In PCI host mode, PCI_SYNC_IN × (1 + CFG_CLKIN_DIV) is the CLKIN frequency.

The *csb_clk* serves as the clock input to the e300 core. A second PLL inside the e300 core multiplies the *csb_clk* frequency to create the internal clock for the e300 core (*core_clk*). The system and core PLL multipliers are selected by the SPMF and COREPLL fields in the reset configuration word low (RCWL), which is loaded at power-on reset or by one of the hard-coded reset options. See the chapter on reset, clocking, and initialization in the *MPC8349EA Reference Manual* for more information on the clock subsystem.

The internal *ddr_clk* frequency is determined by the following equation:

ddr_clk = *csb_clk* × (1 + RCWL[DDRCM])

ddr_clk is not the external memory bus frequency; *ddr_clk* passes through the DDR clock divider (÷2) to create the differential DDR memory bus clock outputs (MCK and $\overline{\text{MCK}}$). However, the data rate is the same frequency as *ddr_clk*.

The internal *lbiu_clk* frequency is determined by the following equation:

lbiu_clk = *csb_clk* × (1 + RCWL[LBIUCM])

lbiu_clk is not the external local bus frequency; *lbiu_clk* passes through the LBIU clock divider to create the external local bus clock outputs (LSYNC_OUT and LCLK[0:2]). The LBIU clock divider ratio is controlled by LCCR[CLKDIV].

In addition, some of the internal units may have to be shut off or operate at lower frequency than the *csb_clk* frequency. Those units have a default clock ratio that can be configured by a memory-mapped register after the device exits reset. Table 56 specifies which units have a configurable clock frequency.

Table 56. Configurable Clock Units

Unit	Default Frequency	Options
TSEC1	*csb_clk/3*	Off, *csb_clk, csb_clk/2, csb_clk/3*
TSEC2, I^2C1	*csb_clk/3*	Off, *csb_clk, csb_clk/2, csb_clk/3*
Security core	*csb_clk/3*	Off, *csb_clk,* csb_clk/2, *csb_clk/3*
USB DR, USB MPH	*csb_clk/3*	Off, csb_clk, csb_clk/2, *csb_clk/3*
PCI1, PCI2 and DMA complex	*csb_clk*	Off, *csb_clk*

Table 57 provides the operating frequencies for the MPC8349EA TBGA under recommended operating conditions (see Table 2).

Table 57. Operating Frequencies for TBGA

Characteristic[1]	400 MHz	533 MHz	667 MHz	Unit
e300 core frequency (*core_clk*)	266–400	266–533	266–667	MHz
Coherent system bus frequency (*csb_clk*)	100–266	100–333	100–333	MHz
DDR1 memory bus frequency (MCK)[2]	100–133	100–133	100–166.67	MHz
DDR2 memory bus frequency (MCK)[3]	100–133	100–133	100–200	MHz
Local bus frequency (LCLK*n*)[4]	16.67–133	16.67–133	16.67–133	MHz
PCI input frequency (CLKIN or PCI_CLK)	25–66	25–66	25–66	MHz
Security core maximum internal operating frequency	133	133	166	MHz
USB_DR, USB_MPH maximum internal operating frequency	133	133	166	MHz

1 The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen so that the resulting *csb_clk*, MCK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies. The value of SCCR[ENCCM], SCCR[USBDRCM] and SCCR[USBMPHCM] must be programmed so that the maximum internal operating frequency of the security core and USB modules does not exceed the respective values listed in this table.
2 The DDR data rate is 2x the DDR memory bus frequency.
3 The DDR data rate is 2x the DDR memory bus frequency.
4 The local bus frequency is 1/2, 1/4, or 1/8 of the *lbiu_clk* frequency (depending on LCCR[CLKDIV]) which is in turn 1x or 2x the *csb_clk* frequency (depending on RCWL[LBIUCM]).

All frequency combinations shown in the table below may not be available. Maximum operating frequencies depend on the part ordered, see Section 22.1, “Part Numbers Fully Addressed by This Document,” for part ordering details and contact your Freescale Sales Representative or authorized distributor for more information.

19.1 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] parameter. Table 58 shows the multiplication factor encodings for the system PLL.

Table 58. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	× 16
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6

Table 58. System PLL Multiplication Factors (continued)

RCWL[SPMF]	System PLL Multiplication Factor
0111	× 7
1000	× 8
1001	× 9
1010	× 10
1011	× 11
1100	× 12
1101	× 13
1110	× 14
1111	× 15

As described in Section 19, "Clocking," the LBIUCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG_CLKIN_DIV configuration input signal select the ratio between the primary clock input (CLKIN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). Table 59 and Table 60 show the expected frequency values for the CSB frequency for select *csb_clk* to CLKIN/PCI_SYNC_IN ratios.

Table 59. CSB Frequency Options for Host Mode

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk* : Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
Low	0010	2 : 1				133
Low	0011	3 : 1			100	200
Low	0100	4 : 1		100	133	266
Low	0101	5 : 1		125	166	333

where:

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)
$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)
$R_{\theta CA}$ = case-to-ambient thermal resistance (°C/W)

$R_{\theta JC}$ is device-related and cannot be influenced by the user. The user controls the thermal environment to change the case-to-ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the air flow around the device, the interface material, the mounting arrangement on printed-circuit board, or change the thermal dissipation on the printed-circuit board surrounding the device.

The thermal performance of devices with heat sinks has been simulated with a few commercially available heat sinks. The heat sink choice is determined by the application environment (temperature, air flow, adjacent component power dissipation) and the physical space available. Because there is not a standard application environment, a standard heat sink is not required.

Table 64 shows heat sink thermal resistance for TBGA of the MPC8349EA.

Table 64. Heat Sink and Thermal Resistance of MPC8349EA (TBGA)

Heat Sink Assuming Thermal Grease	Air Flow	35 × 35 mm TBGA
		Thermal Resistance
AAVID 30 × 30 × 9.4 mm pin fin	Natural convection	10
AAVID 30 × 30 × 9.4 mm pin fin	1 m/s	6.5
AAVID 30 × 30 × 9.4 mm pin fin	2 m/s	5.6
AAVID 31 × 35 × 23 mm pin fin	Natural convection	8.4
AAVID 31 × 35 × 23 mm pin fin	1 m/s	4.7
AAVID 31 × 35 × 23 mm pin fin	2 m/s	4
Wakefield, 53 × 53 × 25 mm pin fin	Natural convection	5.7
Wakefield, 53 × 53 × 25 mm pin fin	1 m/s	3.5
Wakefield, 53 × 53 × 25 mm pin fin	2 m/s	2.7
MEI, 75 × 85 × 12 no adjacent board, extrusion	Natural convection	6.7
MEI, 75 × 85 × 12 no adjacent board, extrusion	1 m/s	4.1
MEI, 75 × 85 × 12 no adjacent board, extrusion	2 m/s	2.8
MEI, 75 × 85 × 12 mm, adjacent board, 40 mm side bypass	1 m/s	3.1

Accurate thermal design requires thermal modeling of the application environment using computational fluid dynamics software which can model both the conduction cooling and the convection cooling of the air moving through the application. Simplified thermal models of the packages can be assembled using the junction-to-case and junction-to-board thermal resistances listed in the thermal resistance table. More detailed thermal models can be made available on request.